

[Name of Document] Abstract

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[Object] In performing an anisotropic etching process after a taper etching process of a
5 gate conductive layer of a two-layer or three-layer laminated structure, a portion that is
not etched is left at an edge of a second conductive film to shorten an LDD region. It is an
object to make the LDD region longer by reducing or removing the left portion that is not
etched.

[Solving Means] After a taper etching process of a gate conductive layer of a two-layer or
10 three-layer laminated structure, an argon plasma treatment is performed. With this argon
plasma treatment, a reactive organism in the taper etching process is removed, and it
becomes possible to reduce or remove the left portion that is not etched in the anisotropic
etching to be performed next.

[Selected Drawing] Fig. 1(D)